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November 2013

# **FQP27N25**

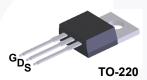
# N-Channel QFET<sup>®</sup> MOSFET 250 V, 25.5 A, 110 m $\Omega$

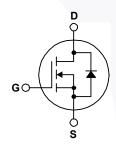
## **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

### **Features**

- 25.5 A, 250 V,  $R_{DS(on)}$  = 110 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 12.75 A
- Low Gate Charge (Typ. 50 nC)
- · Low Crss (Typ. 45 pF)
- · 100% Avalanche Tested





# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQP27N25	Unit
V <sub>DSS</sub>	Drain-Source Voltage		250	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°	C)	25.5	Α
	- Continuous (T <sub>C</sub> = 100	°C)	16.2	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	102	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	600	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	25.5	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	18	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)		180	W
	- Derate above 25°C		1.43	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

# **Thermal Characteristics**

Symbol	Parameter	FQP27N25	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.7	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP27N25	FQP27N25	TO-220	Tube	N/A	N/A	50 units

# **Electrical Characteristics**

T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Uni
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	250			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.29		V/°
I <sub>DSS</sub>	Zoro Coto Voltago Drain Current	V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V			1	μA
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 200 V, T <sub>C</sub> = 125°C			10	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	n/
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	n/
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12.75 A		0.083	0.11	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 12.75 A		24		S
Dynam C <sub>iss</sub>	ic Characteristics			1900	2450	ام
	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		360	470	pF
Coss	Output Capacitance  Reverse Transfer Capacitance	f = 1.0 MHz		45	60	pl
C <sub>rss</sub>	Reverse Transfer Capacitance			40	00	pF
Switch	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 125 V, I <sub>D</sub> = 27 A,		32	75	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		270	550	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			80	170	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	/	120	250	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 200 V, I <sub>D</sub> = 27 A,		50	65	n(
	Gate-Source Charge	V <sub>GS</sub> = 10 V	/ <b></b>	12.5		n(
Q <sub>gs</sub>				26		n(

I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		 	25.5	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode F	orward Current	 	102	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_{S} = 25.5 \text{ A}$	 	1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 27 A,	 220		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs	 1.8	/	μC

- **Notes:**1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. L = 1.5 mH, I<sub>AS</sub> = 25.5 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub>  $\leq$  27 A, di/dt  $\leq$  300 A/µs, V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4. Essentially independent of operating temperature.

# **Typical Characteristics**

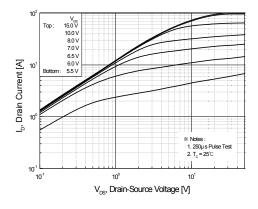
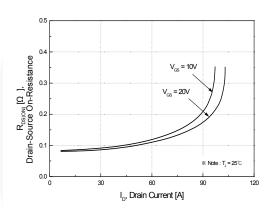


Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



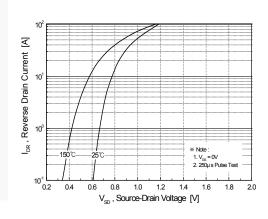
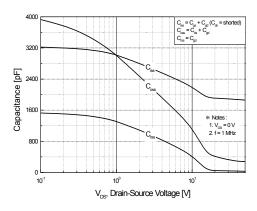


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



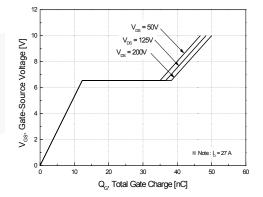
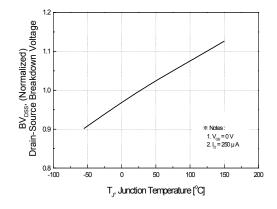


Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

# Typical Characteristics (continued)



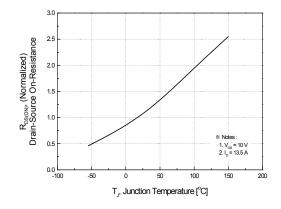
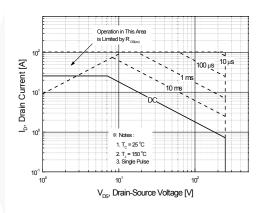


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



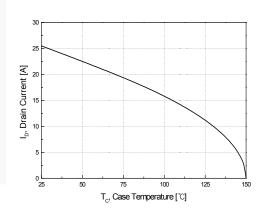


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

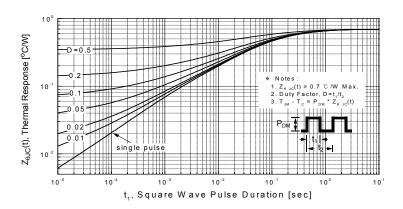


Figure 11. Transient Thermal Response Curve

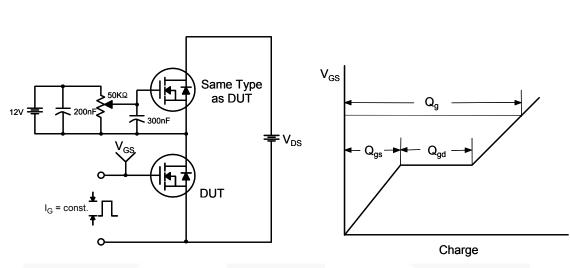


Figure 12. Gate Charge Test Circuit & Waveform

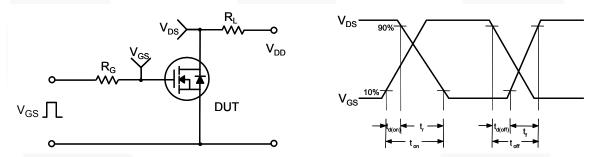


Figure 13. Resistive Switching Test Circuit & Waveforms

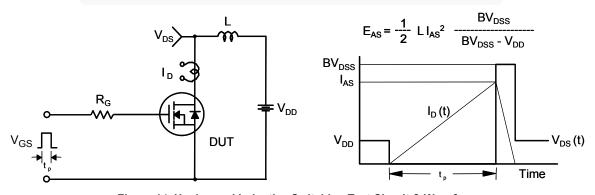
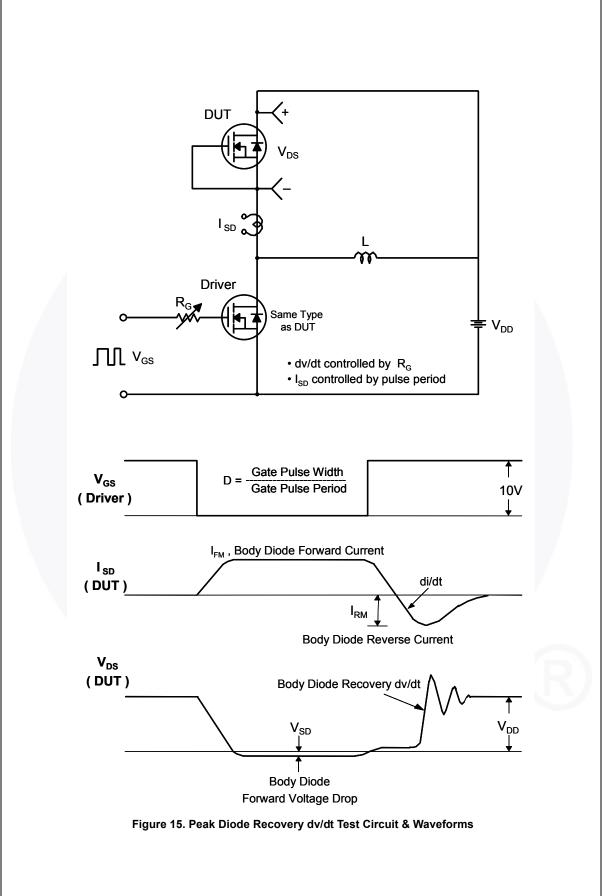


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



# **Mechanical Dimensions**

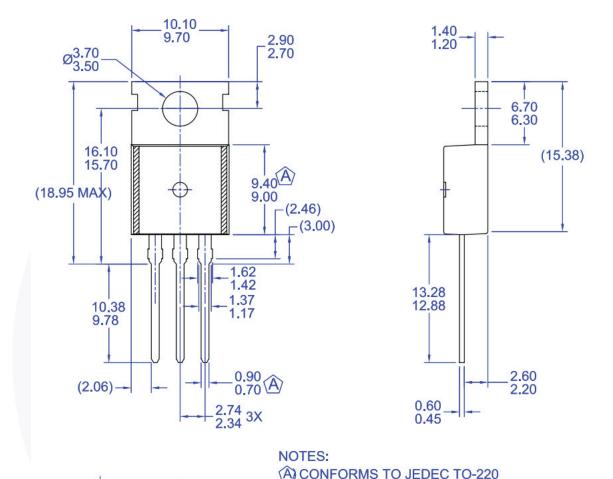


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

VARIATION AB EXCEPT WHERE NOTED

C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

B) ALL DIMENSIONS ARE IN MILLIMETERS.

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